Schottky Barrier Diode

RB715F

Datasheet

●Application

Low current rectification

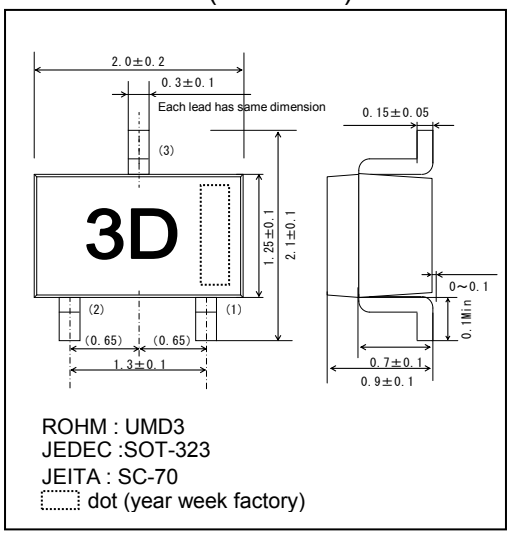
●Features

1) Small mold type. (UMD3)
2) Low V_F
3) High reliability.

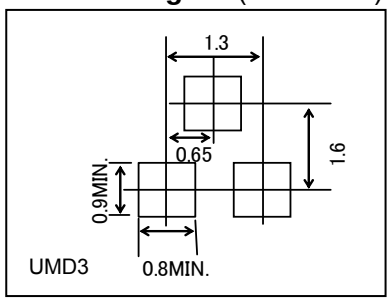
●Construction

Silicon epitaxial planar

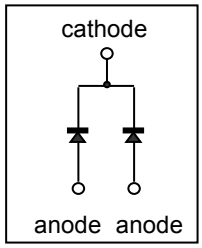
●Dimensions (Unit : mm)



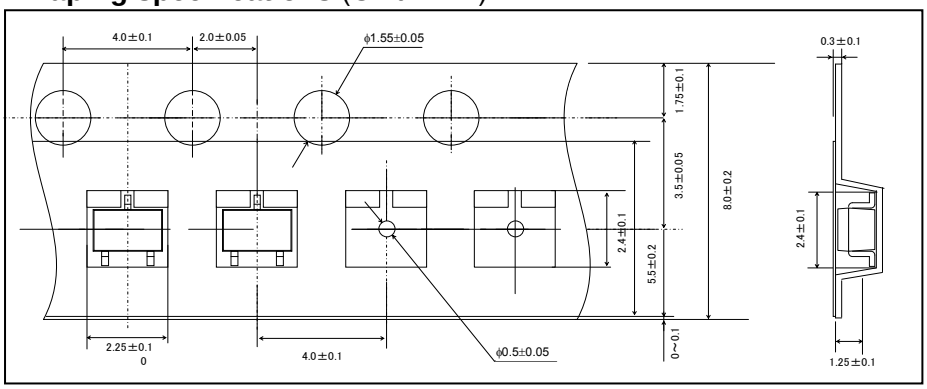
●Land size figure (Unit : mm)



●Structure



●Taping specifications (Unit : mm)



●Absolute maximum ratings (Ta= 25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	Io	30	mA
Forward current surge peak (60Hz・1cyc) (*1)	I_{FSM}	200	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40 to +125	°C

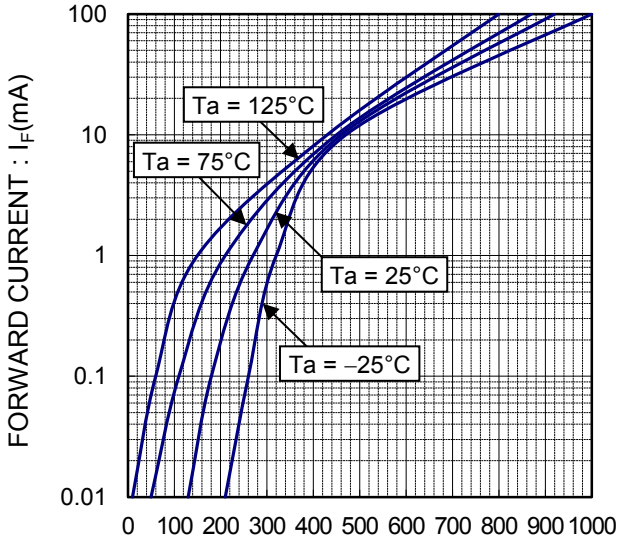
(*1) Rating of per diode

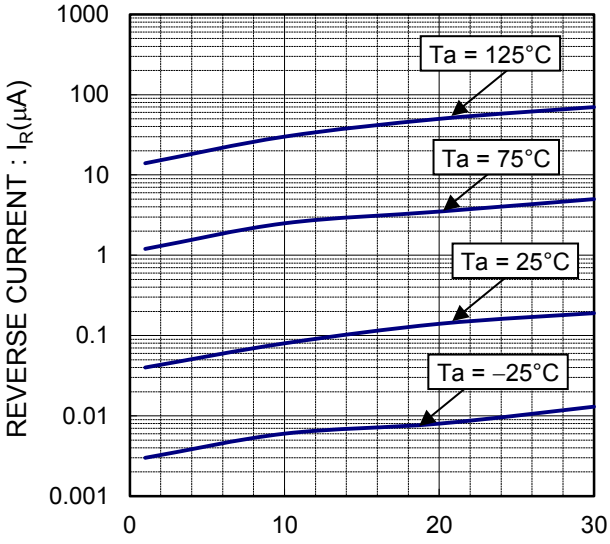
●Electrical characteristics (Ta = 25°C)

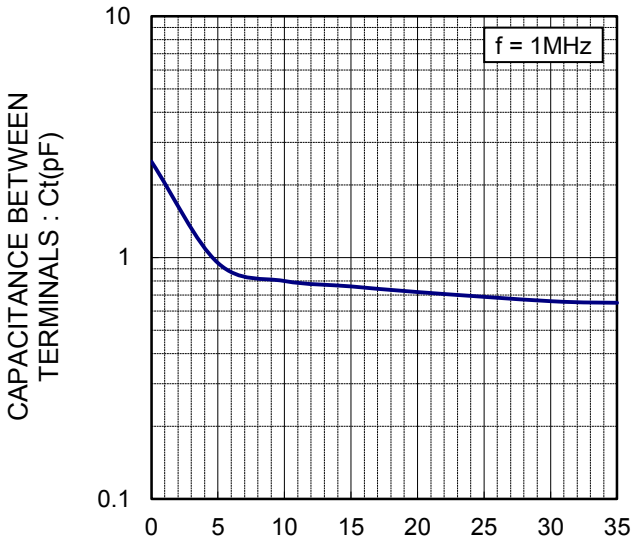
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	I_F=1mA
Reverse current	I_R	-	-	1	μA	V_R=10V
Capacitance between terminals	Ct	-	2.0	-	pF	V_R=1V f=1MHz

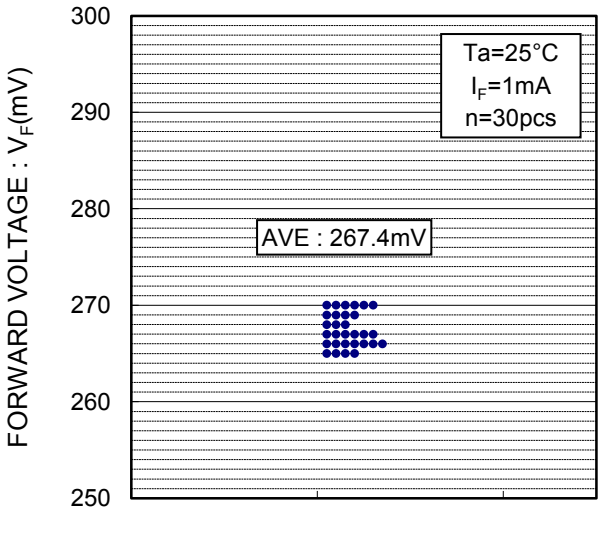
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●Electrical characteristic curves



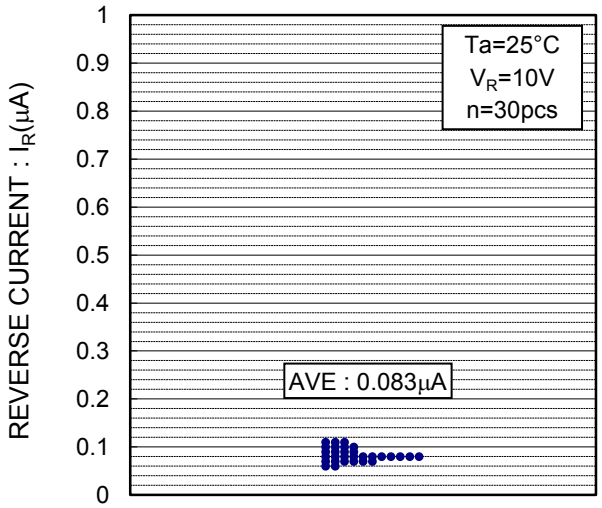




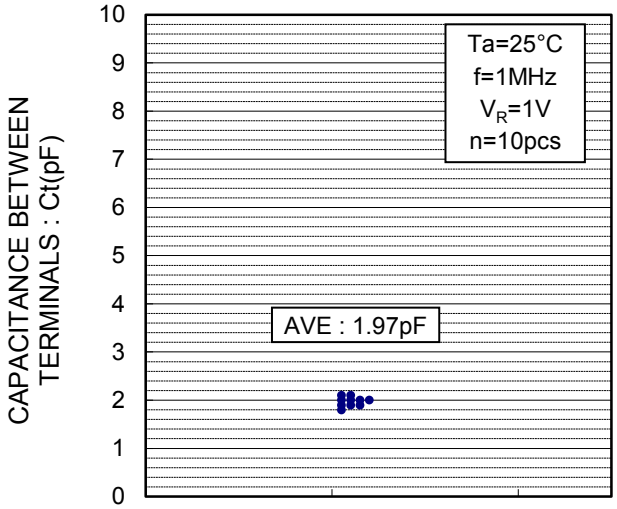


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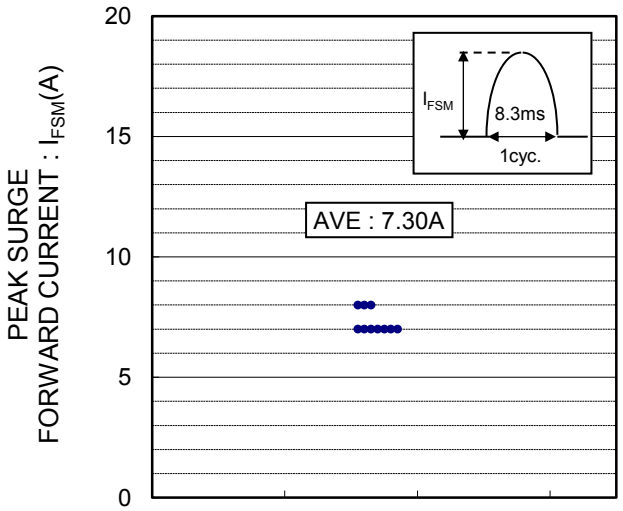
●Electrical characteristic curves



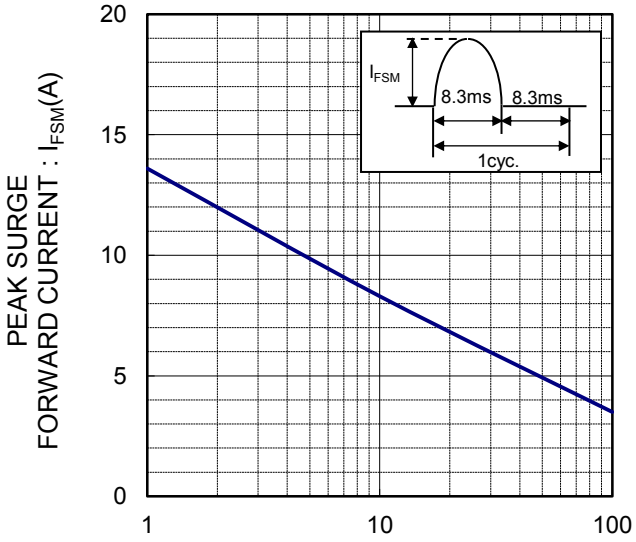
I_R DISPERSION MAP



Ct DISPERSION MAP



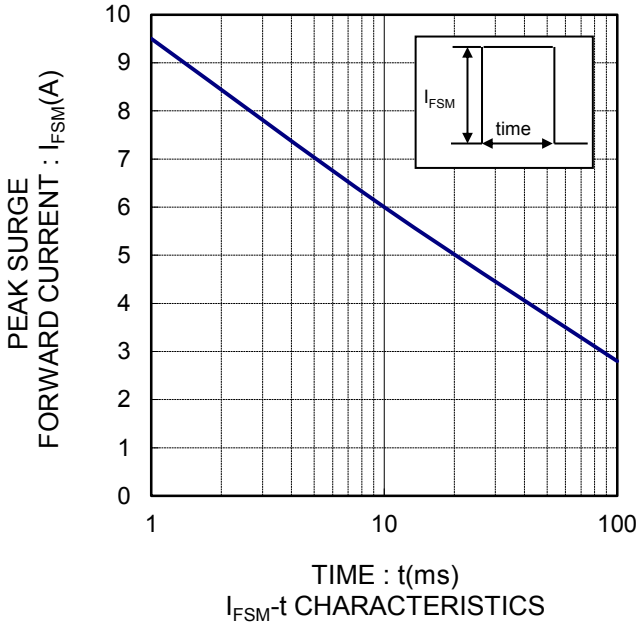
I_{FSM} DISPERSION MAP



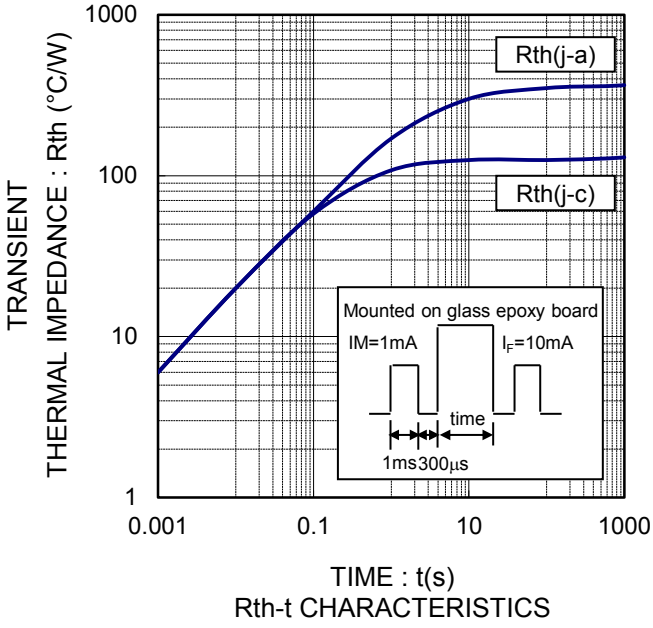
NUMBER OF CYCLES
I_{FSM}-CYCLE CHARACTERISTICS

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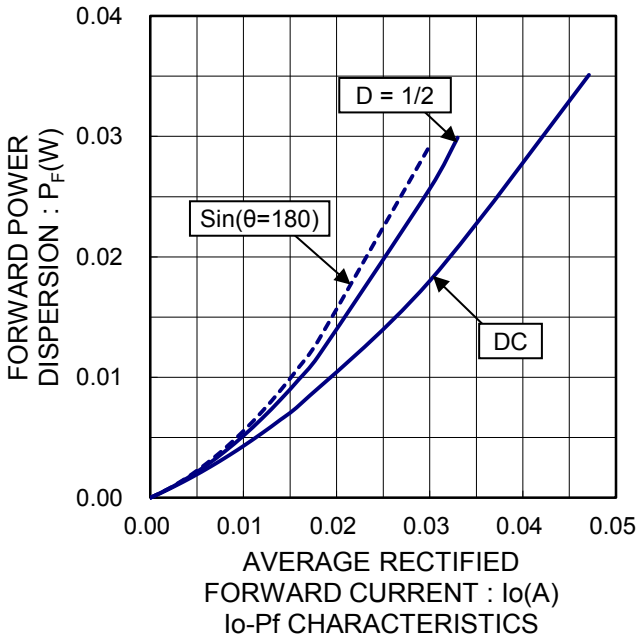
●Electrical characteristic curves



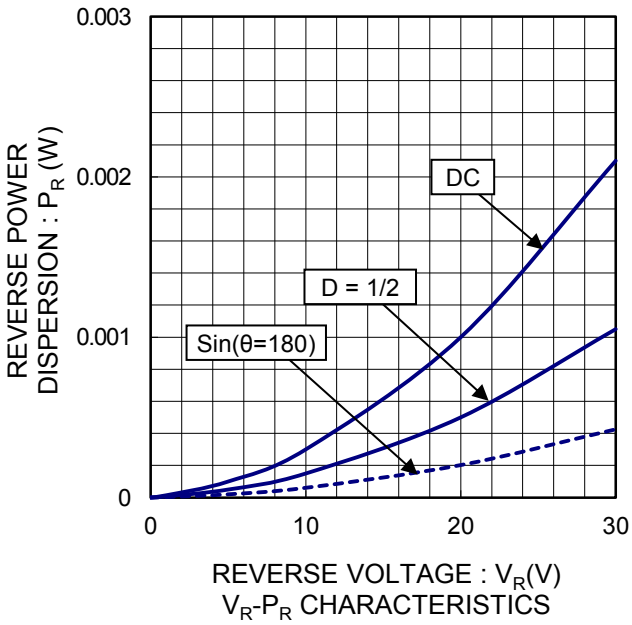
I_{FSM}-t CHARACTERISTICS



Rth-t CHARACTERISTICS



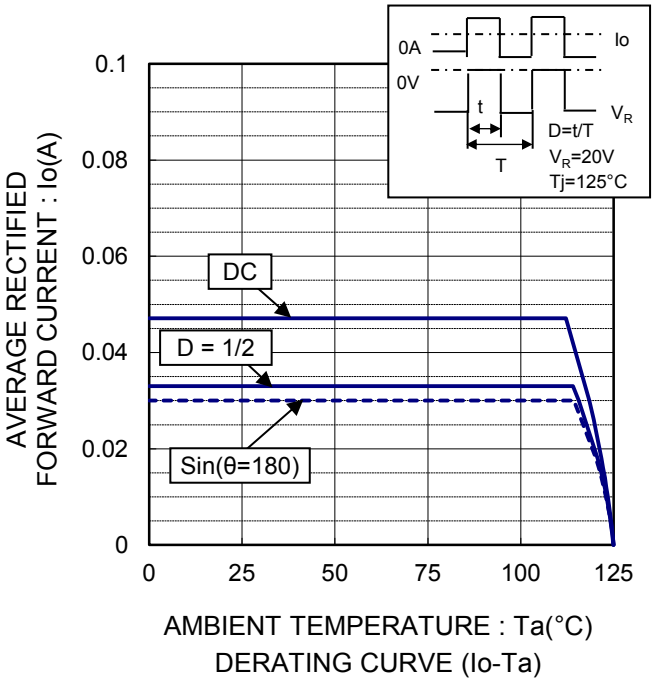
Io-Pf CHARACTERISTICS

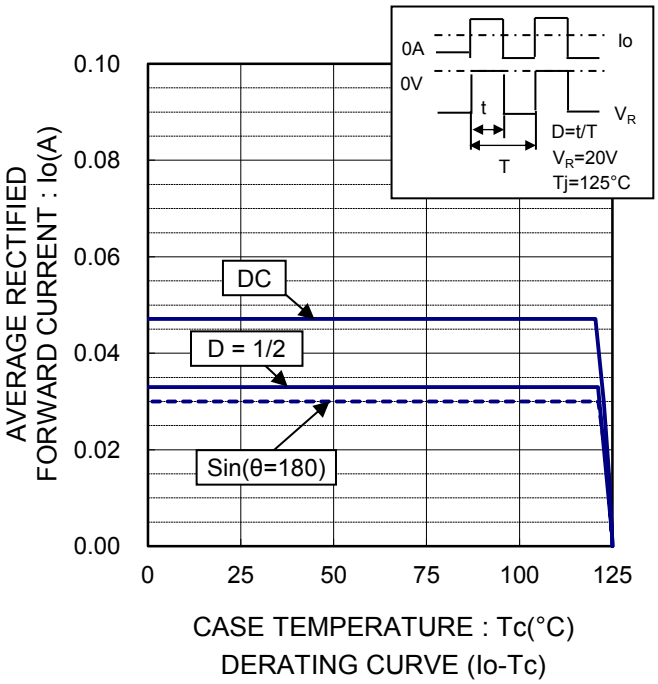


V_R-P_R CHARACTERISTICS

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●Electrical characteristic curves





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